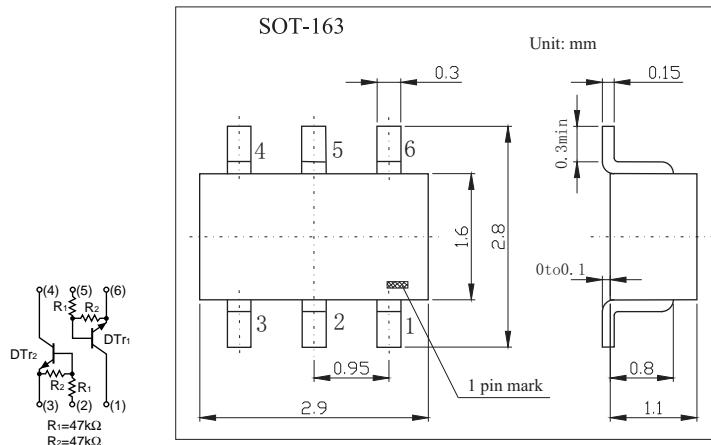


■ Features

- Dual NPN digital transistor



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Supply voltage	Vcc	50	V
Input voltage	VIN	40	V
		-10	
Output current	Io	30	mA
Collector current	Ic(MAX)	100	mA
Power dissipation(Total)	Pd	300	mW
Operating and Storage and Temperature Range	Tj, Tstg	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Input voltage	V _i (off)	V _{cc} =5V, I _o =100μA			0.5	V
	V _i (on)	V _o =0.3V, I _o =2mA	3			V
Output voltage	V _o (on)	I _o =10mA, I _i =0.5mA			0.3	V
Input current	I _i	V _i =5V			0.18	mA
Output current	I _o (off)	V _{cc} =50V, V _i =0V			0.5	μA
DC current gain	G _i	V _o =5V, I _o =5mA	68			
Transition frequency	f _t	V _{ce} =10V, I _e = -5mA , f=100MHz		250		MHz
Input resistance	R _i		32.9	47	61.1	kΩ
Resistance ratio	R ₂ / R ₁		0.8	1	1.2	

■ Marking

Marking	H2
---------	----

■ Typical Characteristics

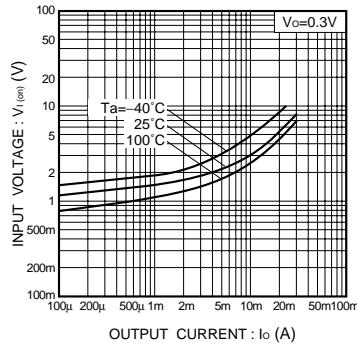


Fig.1 Input voltage vs. output current
(on-characteristics)

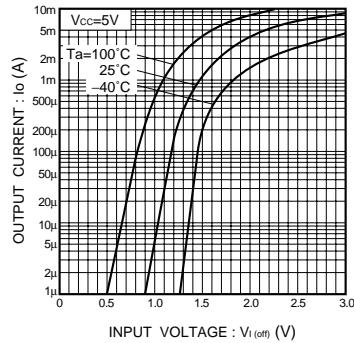


Fig.2 Output current vs. input voltage
(off-characteristics)

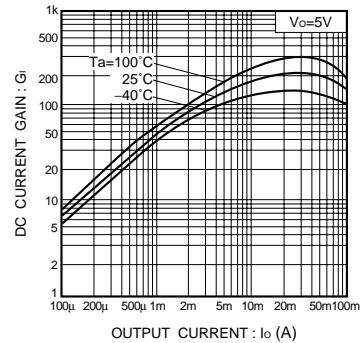


Fig.3 DC current gain vs. output
current

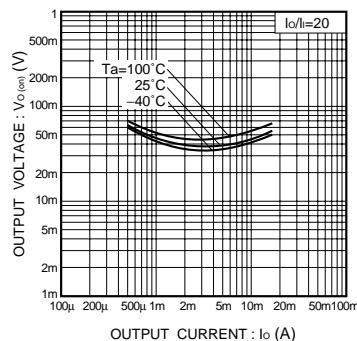


Fig.4 Output voltage vs. output
current